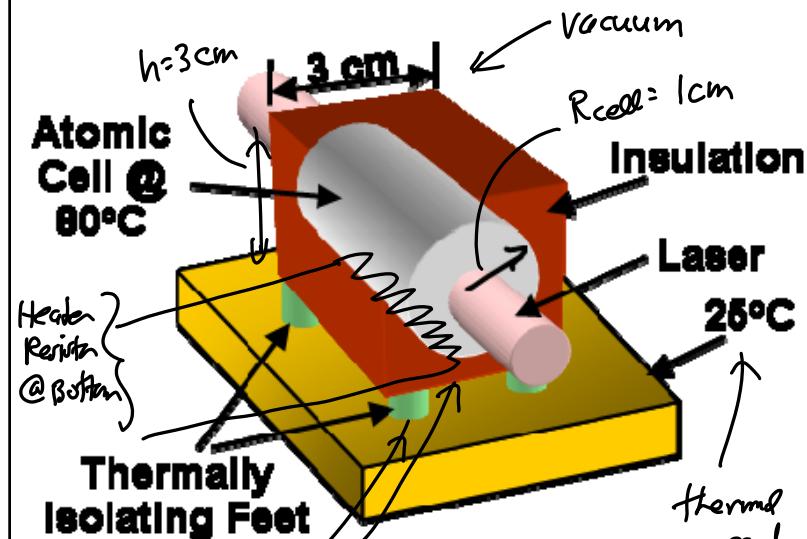


Lecture 5: Scaling Benefits IV & Process Modules I

- Announcements:
 - Make-up lecture (from last Friday) will be placed online soon on the course website
 - HW#1 due next week on Wednesday morning
 - Lecture Module 3 online
 - -----
- Today:
 - Reading: Senturia, Chapter 1
 - Lecture Topics:
 - ↳ Benefits of Miniaturization
 - ↳ Examples
 - GHz micromechanical resonators
 - Chip-scale atomic clock
 - Thermal Circuits
 - Micro gas chromatograph
- Senturia, Chpt. 3; Jaeger, Chpt. 2, 3, 6
 - ↳ Example MEMS fabrication processes
 - ↳ Oxidation
 - ↳ Film Deposition
 - Evaporation
 - Sputter deposition
 - Chemical vapor deposition (CVD)
 - Plasma enhanced chemical vapor deposition (PECVD)
 - Epitaxy
 - Atomic layer deposition (ALD)
 - Electroplating
 - -----
 - Last Time: Thermal circuit modeling

Example: Thermal Cell.

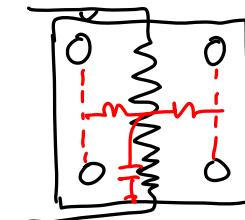
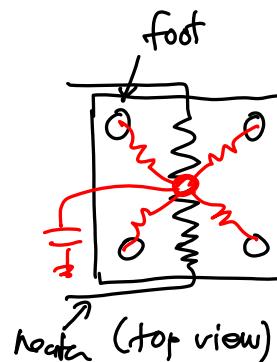
⇒ determine the power needed to get this atomic cell to 80°C (from RT) & how fast

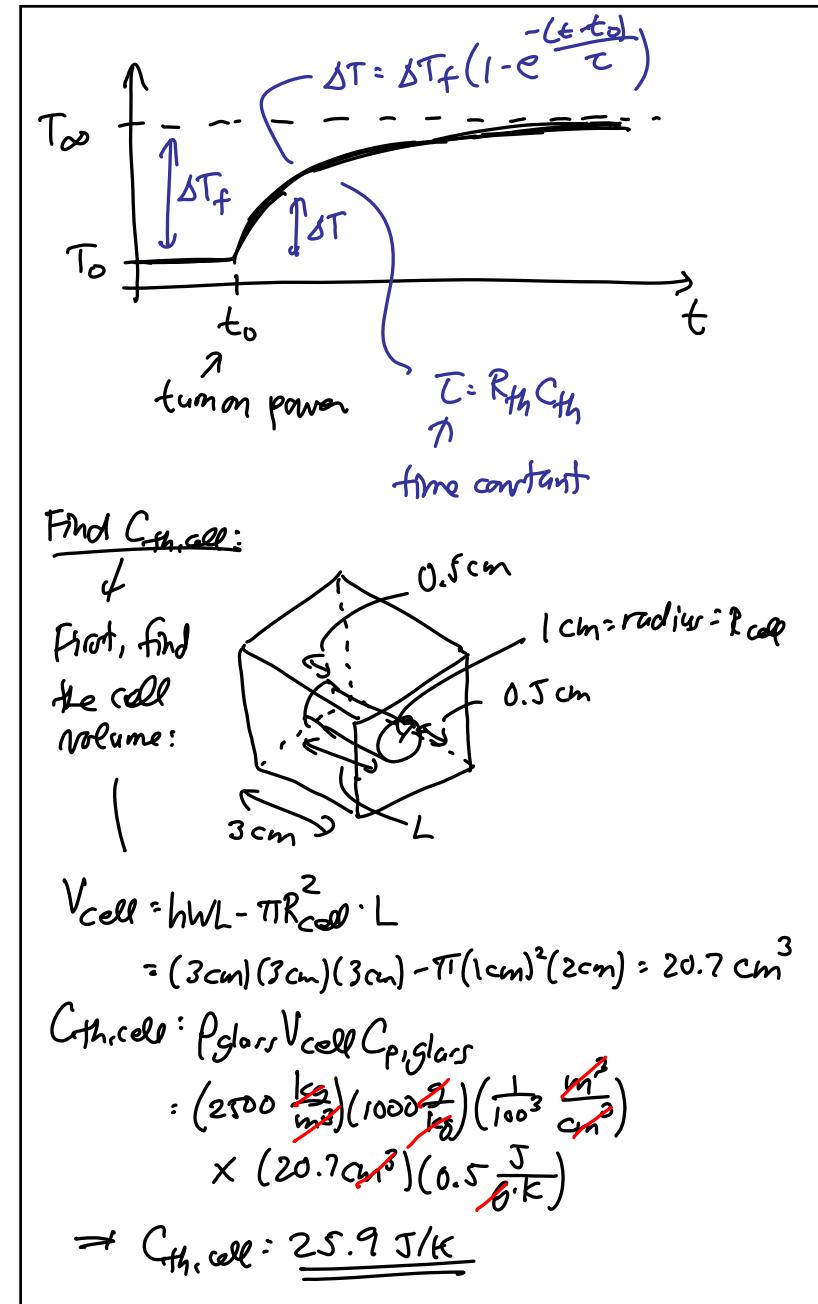
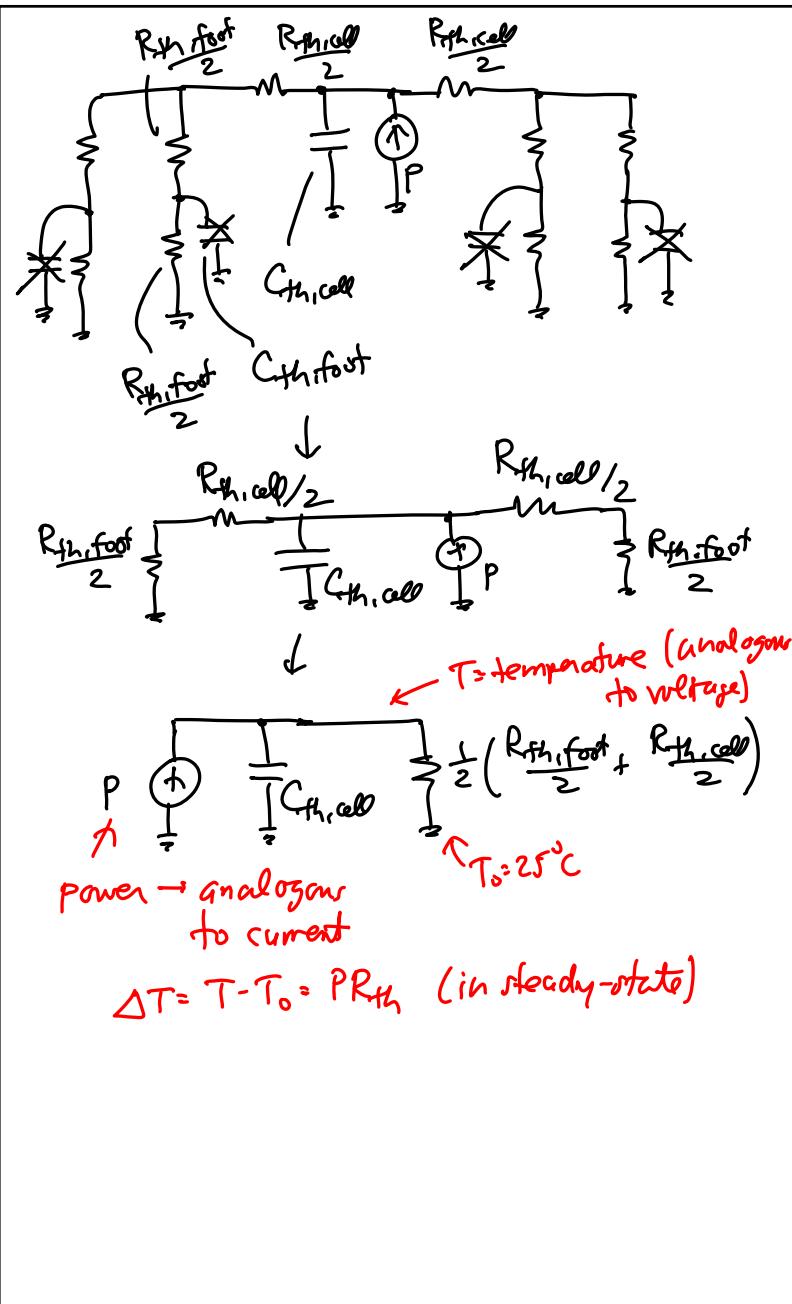


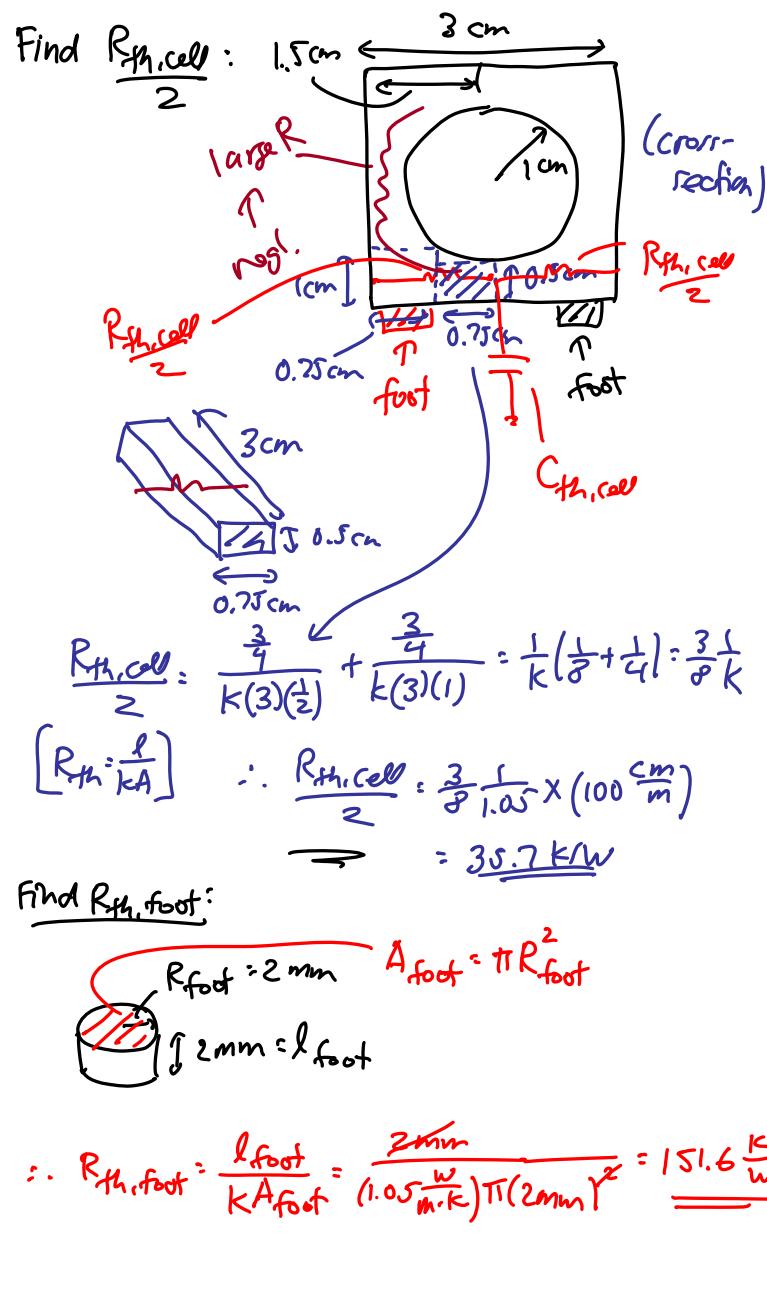
$$\text{all glass: } \rho_{\text{glass}} = 2500 \text{ kg/m}^3$$

$$C_p, \text{glass} = 0.5 \text{ J/(g}\cdot\text{K)}$$

$$k_{\text{glass}} = 1.05 \frac{\text{W}}{\text{m}\cdot\text{K}}$$







Then:

$$R_{th} = \frac{l}{k} \left(\frac{R_{th,foot}}{2} + \frac{R_{th,cell}}{2} \right) = \frac{l}{2} \left(\frac{151.6}{2} + 35.7 \right) \Rightarrow R_{th} = \underline{\underline{55.8 \frac{k}{W}}}$$

\Rightarrow Find the power req'd to maintain $T_\infty = 80^\circ C$ in steady-state:

$$P = \frac{T_\infty - T_0}{R_{th}} = \frac{(80-25)}{55.8} = 0.99W \sim 1W$$

\Rightarrow find the time constant:

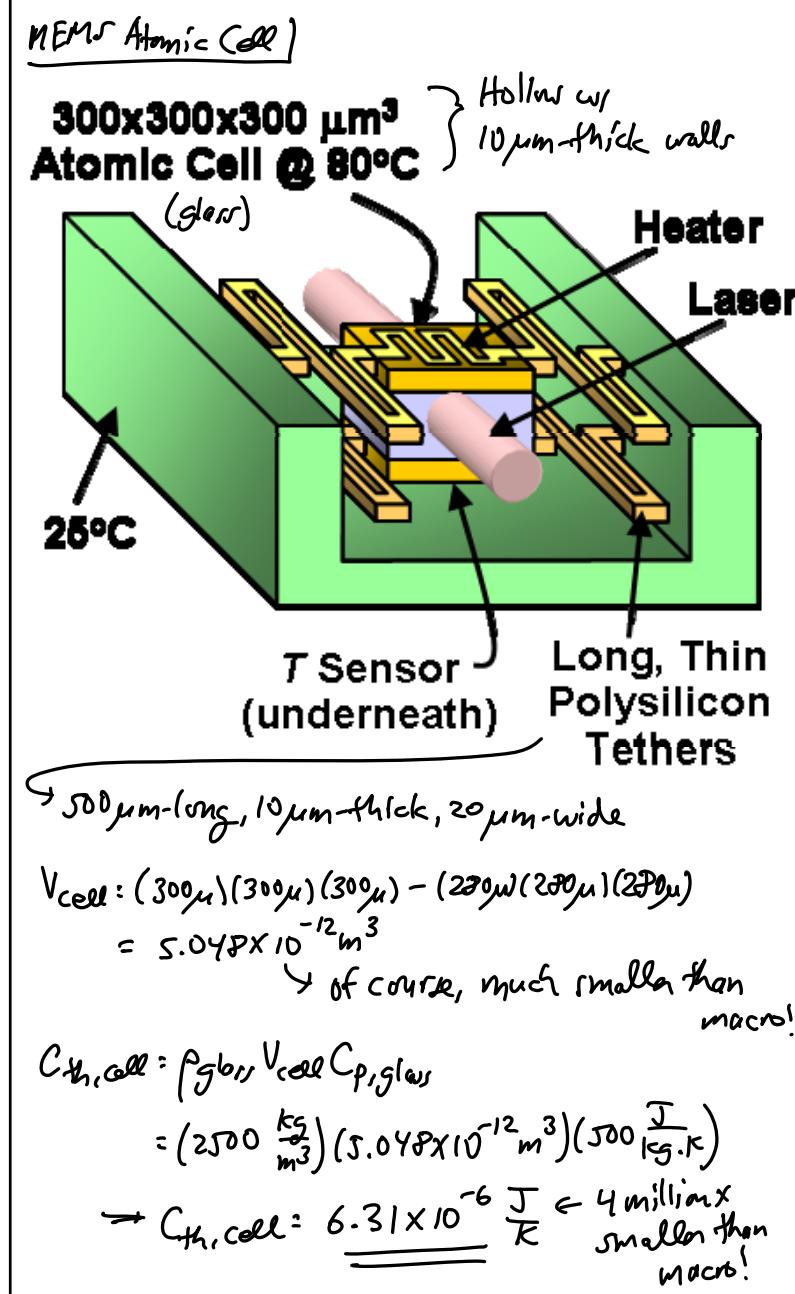
$$\tau = R_{th} C_{th,cell} = 24 \text{ min.}$$

\Rightarrow If takes $\sim 3\tau$ to reach steady-state
 \therefore must wait 72 min. before using this atomic cell

How about the MEMS case?

\rightarrow much smaller cell volume \rightarrow weight \downarrow

\Rightarrow can use long, thin supports: $L \uparrow, A \downarrow \rightarrow R_{th} \uparrow$



$$R_{th, \text{supp}}: \frac{l_{\text{supp}}}{k_{\text{polySi}} W_{\text{supp}} h_{\text{supp}}} = \frac{500 \mu\text{m}}{(30 \frac{\text{W}}{\text{m}\cdot\text{K}})(20 \mu\text{m})(10 \mu\text{m})}$$

$$\Rightarrow R_{th, \text{supp}}: \underline{\underline{83,333 \text{ K/W}}} \leftarrow 548 \times \text{larger!}$$

and...

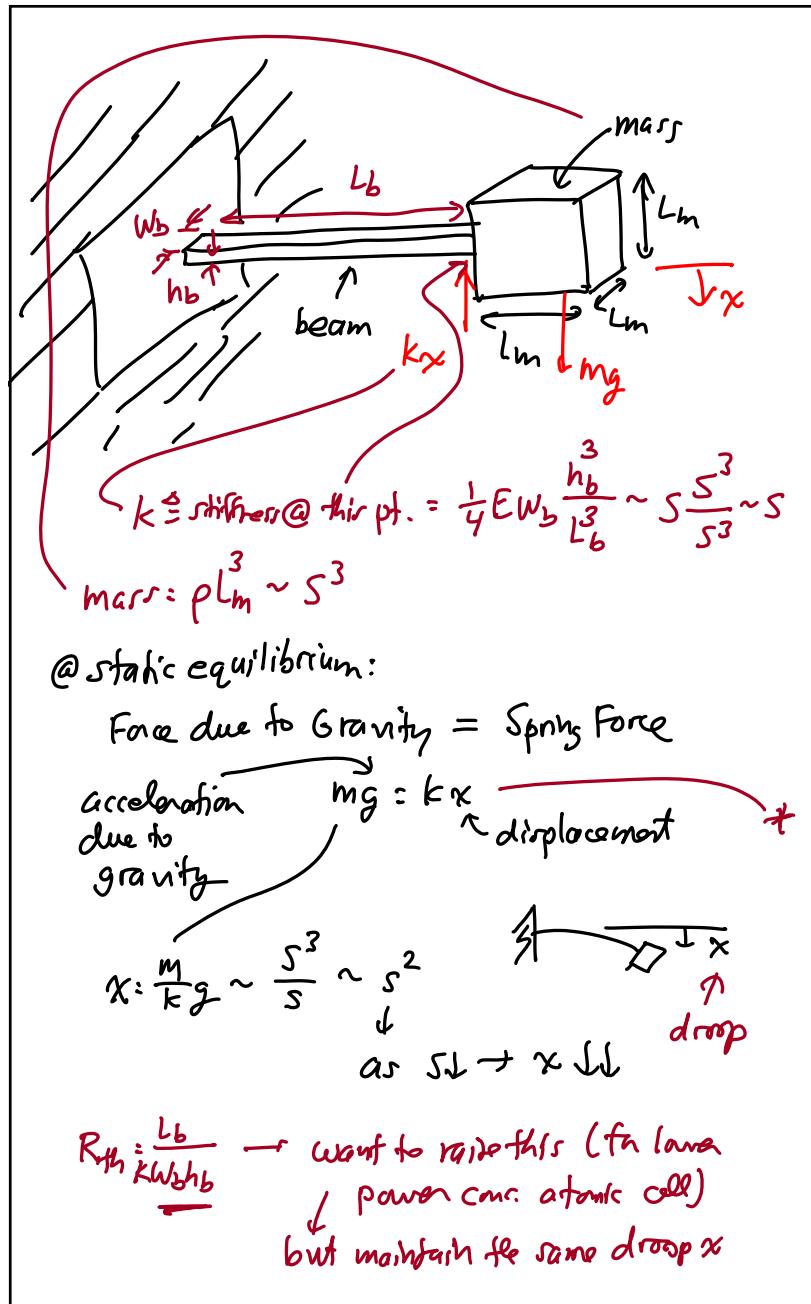
$$P: \frac{(80-25)}{83,333} = \underline{\underline{2.64 \text{ mW}}} \leftarrow 548 \times \text{smaller!}$$

$$T: \underline{\underline{0.135}} \leftarrow 7300 \times \text{faster}$$

All due to scaling!

What makes all of this possible?

- ① Scaling reduces $C_{th} \sim l^3 \rightarrow s^3 \downarrow \rightarrow C_{th} \downarrow \downarrow$
- ② Scaling allows the use of long, thin tethers $\downarrow R_{th} \uparrow \uparrow$



$$\begin{aligned} * \rightarrow \rho L_m^3 g &= \frac{1}{4} E w_b \frac{h_b^3}{L_b^3} x \\ \frac{L_b}{w_b h_b} &= \frac{1}{4} E \frac{h_b^2}{L_b^2} x \frac{1}{\rho L_m^3 g} \sim \frac{S^2}{S^2} \frac{1}{S^3} \sim \frac{1}{S^3} \\ \uparrow & \text{const.} \\ \sim R_{th} & \\ \text{as } S \downarrow \rightarrow \frac{L_b}{w_b h_b} &\sim R_{th} \uparrow \uparrow \end{aligned}$$